Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN2110A

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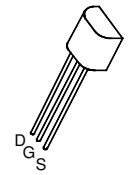
FEATURES

* 100 Volt V_{DS}
* $R_{DS(on)}$= 4Ω



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

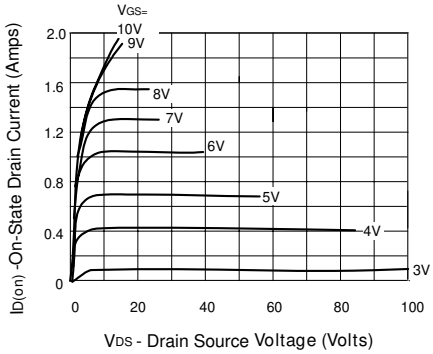
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current at T_{amb}=25°C	I_D	320	mA
Pulsed Drain Current	I_{DM}	6	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at T_{amb}=25°C	P_{tot}	700	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

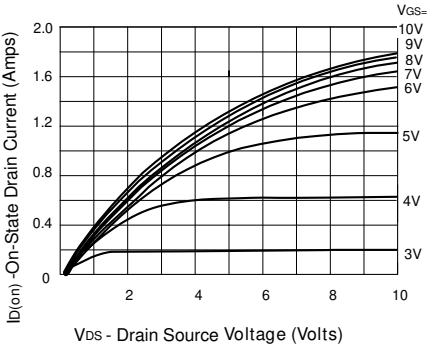
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	I_D=1mA, V_{GS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	ID=1mA, V_{DS}= V_{GS}
Gate-Body Leakage	I_{GSS}		20	nA	V_{GS}=± 20V, V_{DS}=0V
Zero Gate Voltage Drain Current	I_{DSS}		1 100	µA µA	V_{DS}=100V, V_{GS}=0 V_{DS}=80V, V_{GS}=0V, T=125°C(2)
On-State Drain Current(1)	$I_{D(on)}$	1.5		A	V_{DS}=25V, V_{GS}=10V
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		4	Ω	V_{GS}=10V,I_D=1A
Forward Transconductance (1)(2)	g_{fs}	250		mS	V_{DS}=25V,I_D=1A
Input Capacitance (2)	C_{iss}		75	pF	V_{DS}=25 V, V_{GS}=0V, f=1MHz
Common Source Output Capacitance (2)	C_{oss}		25	pF	
Reverse Transfer Capacitance (2)	C_{rss}		8	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	V_{DD}≈25V, I_D=1A
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		13	ns	
Fall Time (2)(3)	t_f		13	ns	

(1) Measured under pulsed conditions. Width=300µs. Duty cycle ≤2%
(2) Sample test
(3) Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator

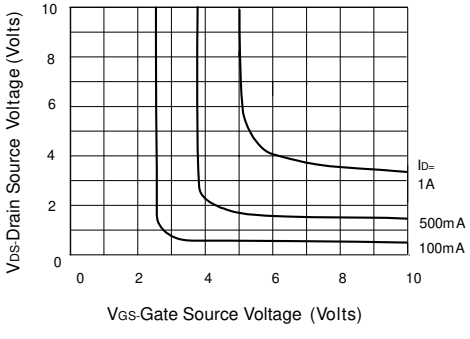
TYPICAL CHARACTERISTICS



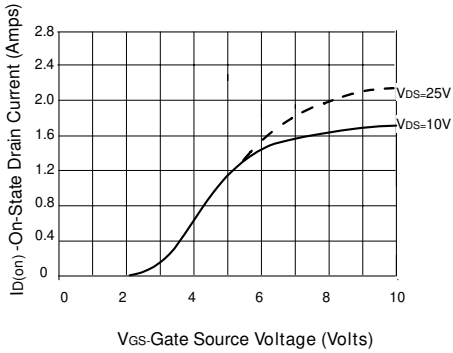
Output Characteristics



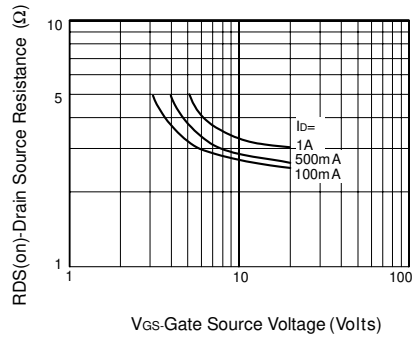
Saturation Characteristics



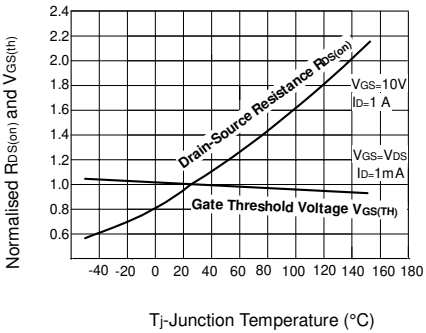
Voltage Saturation Characteristics



Transfer Characteristics



On-resistance v gate-source voltage



Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v Temperature

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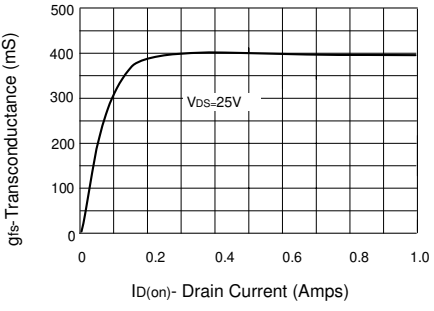
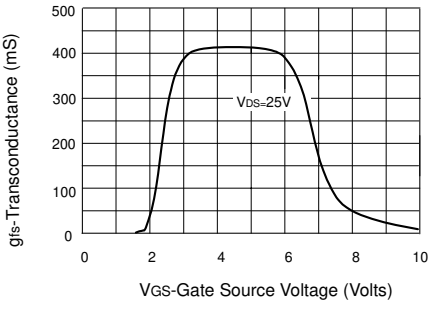
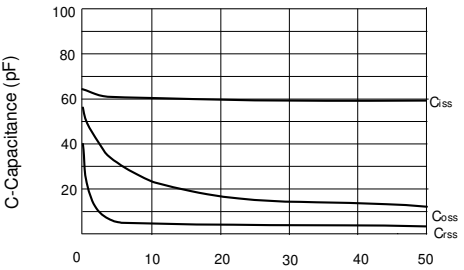
TYPICAL CHARACTERISTICS



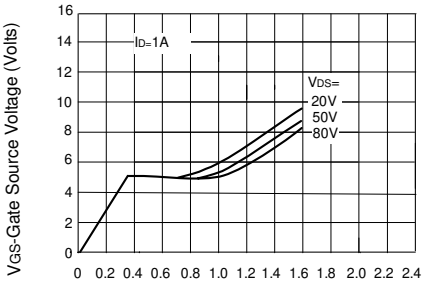
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage